

3CG 2013 MEETING

June 10-13, 2013

The Westin Resort & Spa, Cancun, Mexico

Room A

Conference Onsite Registration

The Westin Resort & Spa

14:00 - 18:00 PM

June 9

3CG 2013 Meeting June 10

7:20 – 8:20	Breakfast	
Monday June 10 8:20 - 8:30 AM	Opening	
Monday June 10	ROOM A: Session 1 (MBE)	Chair: Ikai Lo
8:30 – 9:00 AM	A1: Direct determination of stress evolution during hetero-epitaxial growth	Hidehito Asaoka Japan Atomic Energy Agency (JAEA), Japan
9:00 – 9:30 AM	A2: Wide-range control of emission wavelengths of InAs/GaAs QDs grown by MBE towards ultra-broadband NIR light source for biomedical imaging	Nobuhiko Ozaki Wakayama University, Japan
9:30 – 10:00 AM	A3: MBE growth of high-dispersive mirrors for sub-picosecond lasers	Agata Jasik Institute of Electron Technology, Poland
10:00 – 10:30 AM	SESSION BREAK	

Conference Program Schedule Room A –3CG 2013 Meeting

Monday June 10	ROOM A: Session 2 (Epitaxy)	Chair: Nobuhiko Ozaki
10:30 – 11:00 AM	A4: Ni(111)/graphene/Y ₂ O ₃ (111) heterostructures by combined CVD and reactive MBE growth	Matthias Batzill University of South Florida, USA
11:00 – 11:30 AM	A5: The growth of GaN micropylar and microdisk by plasma-assisted molecular beam epitaxy	Ikai Lo National Sun Yat-Sen University, Taiwan
11:30 – 12:00 AM	A6: Assessment of a nanocrystal 3D morphology by the analysis of single HAADF-HRSTEM images	Antonio J. Ramirez Brazilian Nanotechnology National Laboratory, Brazil
12:00 – 14:00 PM	LUNCH BREAK	
Monday June 10	ROOM A: Session 3 (Nucleation)	Chair: Babak Nikoobakht
14:00 – 14:30 PM	A7: Effects of temperature and flow in nucleation and domain growth, a theoretical approach	Iván Santamaría-Holek Universidad Nacional Autónoma de México, Mexico
14:30 – 15:00PM	A8: Nanoparticles for controlling nucleation and crystallisation	Jerry Heng Imperial College London, United Kingdom
15:00 – 15:30PM	A9: In-Situ studies of apatite formation in water	Casper Steenberg Ibsen Aarhus University, Denmark
15:30 – 16:00PM	SESSION BREAK	
Monday June 10	ROOM A: Session 4 (MOVPE)	Chair: Jerry Heng
16:00 – 16:30PM	A10: Formation of inversion domain structure in MOVPE AlN thin layers grown on a sapphire substrate	Noriyuki Kuwano Malaysia-Japan International Institute of Technology (MJIT), Malaysia
16:30 – 17:00PM	A11: Impact of the crystal symmetry on orientation and directed-assembly of laterally grown cubic and hexagonal nanowires and heterojunctions	Babak Nikoobakht National Institute of Standards and Technology, USA
17:00 – 17:30PM	A12: Selective area MOVPE of vertical and lateral InAs nanowires on silicon substrates	Kamil Sladek Peter Grunberg Institut (PGI-9), Germany

Conference Program Schedule Room A –3CG 2013 Meeting

3CG 2013 Meeting June 11		
7:30 – 8:30	Breakfast and Poster	
Tuesday June 11	ROOM A: Session 5 (General)	Chair: Mukannan Arivanandhan
8:30 – 9:00 AM	A13: Intercalation and defects in epitaxial graphene on a metal	Johann Coraux CNRS & Université Joseph Fourier, France
9:00 – 9:30 AM	A14: Growth of Layered Crystals	Zhengdong Cheng Texas A&M University, USA
9:30 – 10:00 AM	A15: First steps of the semiconductor nanostructure formation	Gregorio Hernández Cocoletzi University City - BUAP, Mexico
10:00 – 10:30 AM	SESSION BREAK	
Tuesday June 11	ROOM A: Session 6 (General)	Chair: Johann Coraux
10:30 – 11:00 AM	A16: Combinatorial Substrate Epitaxy: A high throughput method for determining phase and orientation relationships in thin film growth.	Gregory S. Rohrer Carnegie Mellon University, USA
11:00 – 11:30 AM	A17: Layered mixed-anion compounds: Epitaxial growth, active function exploration, and device application	Hidenori Hiramatsu Tokyo Institute of Technology, Japan
11:30 – 12:00 AM	A18: Suppression of light induced degradation in B-doped Czochralski grown silicon by Ge codoping	Mukannan Arivanandhan Shizuoka University, Japan
12:00 - 14:00 PM	LUNCH BREAK	
Tuesday June 11	ROOM A: Session 7 (Nano)	Chair: Robert Edgington
14:00 – 14:30 PM	A19: Growth and optoelectronic properties of Silicon quantum dots	Jun Xu Nanjing University, China

Conference Program Schedule Room A –3CG 2013 Meeting

14:30 – 15:00 PM	A20: Mass transport and material re-organization during growth and capping of semiconductor quantum dots	Holger Eisele Technische Universität Berlin, Germany
15:00 – 15:30 PM	A21: Study Of One Dimensional Nanocrystal Growth Using Anodic Aluminium Oxide	Jinghua Fang CSIRO Materials Science and Engineering, Australia
15:30-16:00 PM	SESSION BREAK	
Tuesday June 11	ROOM A: Session 8 (General)	Chair: Holger Eisele
16:00 – 16:30 PM	A22: Recent Progresses in Protein Crystallogenesi in NWPU	Da-Chuan Yin Northwestern Polytechnical University, China
16:30 – 17:00 PM	A23: Crystal growth and evolution of calcium pyrophosphates of biological interest	Christele Combes Universitaire de Recherche et d'Ingénierie des Matériaux, France
17:00 – 17:30 PM	A24: Growth and Assembly of Collagen on Surfaces	Cristian V. Ciobanu Colorado School of Mines, USA
17:30 – 18:00 PM	A25: Cell adhesion on diamond: crystallinity matters	Robert Edgington University College London, United Kingdom
3CG 2013 Meeting June 12		
7:30 – 8:30	Breakfast and Poster	
Wednesday June 12	ROOM A: Session 9 (Nanocrystals)	Chair: Paola Prete
8:30 – 9:00 AM	A26: Morphological control of titanium dioxide nanocrystals by solvothermal method employing water-soluble titanium complexes	Makoto Kobayashi Tohoku University, Japan
9:00 - 9:30 AM	A27: Synthesis of monodispersed tungsten bronze Nano crystals by solvothermal reaction	Tsugio Sato Tohoku University, Japan

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9:30 – 10:00 AM	A28: Crystal growth and optoelectronics in quantum nanostructures on nonpolar oxides	Hiroaki Matsui University of Tokyo, Japan
10:00 – 10:30 AM	SESSION BREAK	
Wednesday June 12	ROOM A: Session 10 (General)	Chair: Hiroaki Matsui
10:30 – 11:00 AM	A29: Growth of nanowires by high temperature glancing angle disposition	Motofumi Suzuki Kyoto University, Japan
11:00 – 11:30 AM	A30: MOVPE self-assembly of III-V nanowires: advances in growth control and device fabrication	Paola Prete CNR-IMM Lecce Research Unit, Italy
11:30 – 12:00 AM	A31: Molecular “photomagnetic” conductors	Toshio Naito Ehime University, Japan
12:00 - 14:00 PM	LUNCH BREAK	
Wednesday June 12	ROOM A: Session 11 (Theory)	Chair: Antonio Viviani
14:00 – 14:30 PM	A32: Discovery of Organic Conductors and Small Band-gap Semiconductors:A High Throughput DFT Study	Bohdan Schatschneider The Pennsylvania State University, USA
14:30 – 15:00 PM	A33: Modeling and Optimization of the thermal design in the growth process of SiC	Qi-Sheng Chen Institute of Mechanics, Chinese Academy of Sciences, China
15:00 – 15:30 PM	A34: Theoretical design of stack structure for resistive random access memories	Katsumasa Kamiya University of Tsukuba, Japan
15:30 – 16:00 PM	SESSION BREAK	
Wednesday June 12	ROOM A: Session 12 (Theory)	Chair: Katsumasa Kamiya
16:00 – 16:30 PM	A35: Burnett Equations for Fluid Flow Modelling in Vapour Crystal Growth	Antonio Viviani Seconda Università di Napoli, Italy

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16:30 – 17:00 PM	A36: Determination of specific surface free energy of inorganic crystal using contact angle of liquid	Takaomi Suzuki Shinshu University, Japan
17:00 – 17:30 PM	A37: An accurate assessment of the binding energy of various alloying elements with ferrite/austenite interfaces: a recent advance in the modeling of migrating interfaces	Hugo Van Landeghem McMaster University, Canada
Thursday June 13	Social Network Events	

3CG 2013 MEETING

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Room B

Conference Onsite Registration

The Westin Resort & Spa

14:00 - 18:00 PM

June 9

3CG 2013 Meeting June 10

7:20 – 8:20	Breakfast	
Monday June 10 8:20 - 8:30 AM	Opening	
Monday June 10	Room B: Session 1 (Nanostructural)	Chair: Eva Rauls
8:30 – 9:00 AM	B1: Nucleation and growth take into account physical properties of nanoparticles	Yuki Kimura Tohoku University, Japan
9:00 – 9:30 AM	B2: Growth and characterization of homojunctions based on ZnO nanowires for nanoscale light sources	Jianlin Liu University of California, USA
9:30 – 10:00 AM	B3: In situ atomic observation of E-beam assisted nanostructural growth under electron microscope	Jianbo Wang Wuhan University, China
10:00 – 10:30	SESSION BREAK	
Monday June 10	Room B: Session 2 (Nano)	Chair: Yuki Kimura

Conference Program Schedule Room B – 3CG 2013 Meeting

10:30 – 11:00 AM	B4: A self-powered UV detector based on ZnO nanoneedles/H ₂ O solid-liquid heterojunction	Yanxue Chen Shandong University, China
11:00 – 11:30 AM	B5: Highly incline-oriented growth of layered cobaltite Ca _x CoO ₂ thin films and its application to fast bolometric sensors utilizing the off-diagonal thermoelectric effect	Kouhei Takahashi Advanced Technology Research Laboratories, Panasonic Corporation, Japan
11:30 – 12:00 AM	B6: Precipitation induced growth of SiC clusters in ion implanted Silicon	Eva Rauls Universitaet Paderborn, Germany
12:00 - 14:00 PM	LUNCH BREAK	
Monday June 10	Room B: Session 3 (Nanostructure)	Chair: Alexander Gelfgat
14:00 – 14:30 PM	B7: Supramolecular assemblies based on <i>p</i> -sulfonatothiocalix [6] arene complexes with metal ions and water molecules	Fumio Hamada Akita University, Japan
14:30 – 15:00 PM	B8: Alkaline-earth borates & oxides: wet-chemistry based thermal conversion route synthesis, properties and applications.	Wancheng Zhu Qufu Normal University, China
15:00 – 15:30 PM	B9: Weak Intramolecular Hydrogen Bonding in Aromatic Molecules. A Crystallographic Investigation	Zhanting Li Fudan University, China
15:30 – 16:00 PM	SESSION BREAK	
Monday June 10	Room B: Session 4 (General)	Chair: Fumio Hamada
16:00 – 16:30 PM	B10: Symmetry and the polar state of condensed molecular matter: theory and experimental facts	Jürg Hulliger University of Berne, Switzerland
16:30 – 17:00 PM	B11: Structure of amorphous CaCO ₃ precursor and its relationship to polymorphs: atomistic simulation study	Hiroki Nada National Institute of Advance Industrial Science and Technology, Japan
17:00 – 17:30 PM	B12: Destabilization of convection in Czochralski melt flow by slow rotation and by low-amplitude oscillations of crucible wall temperature	Alexander Gelfgat Tel Aviv University, Israel

Conference Program Schedule Room B – 3CG 2013 Meeting

3CG 2013 Meeting June 11		
7:30 – 8:30	Breakfast and Poster	
Tuesday June 11	Room B: Session 5 (Nano Device)	Chair: Alexandra Pena Revellez
8:30 – 9:00 AM	B13: Piezotronics and Piezo-phototronics	Zhong Lin Wang Georgia Institute of Technology, USA
9:00 – 9:30 AM	B14: 3-dimensional nano structures for photonics devices	Jong-Lam Lee Pohang University of Science and Technology, Korea
9:30 – 10:00 AM	B15: Use of Low-Phonon Crystalline Hosts for Rare Earth-Doped Mid-infrared Lasers and Phosphors	Joseph Ganem Loyola University Maryland, USA
10:00 – 10:30 AM	SESSION BREAK	
Tuesday June 11	Room B: Session 6 (Oxide)	Chair: Jong-Lam Lee
10:30 – 11:00 AM	B16: Atomic and electronic structure of Mn-doped Ga ₂ O ₃ thin film and interface with MgAl ₂ O ₄ substrate	Hiroyuki Hayashi Kyoto University, Japan
11:00 – 11:30 AM	B17: Periodically domain-structured KTiOPO ₄ crystals grown from high temperature solution	Alexandra Pena Revellez Institut Néel – CNRS / UJF, France
11:30 – 12:00 AM	B18: Superionic Conducting Glass-Ceramics of Silicophosphates: Crystallization Kinetics and Conduction Properties	Toshinori Okura Kogakuin University, Japan
12:00 – 14:00 PM	LUNCH BREAK	
Tuesday June 11	Room B: Session 7 (Oxide Thin Film)	Chair: Keisuke Ohdaira
14:00 – 14:30 PM	B19: Oxide thin film growth by pulsed laser deposition: Effects of postannealing.	Kosuke Matusuzaki Tokyo Institute of Technology, Japan
14:30 – 15:00 PM	B20: A study on surface morphology and optical properties of Copper Sulphide thin films deposited by vacuum evaporation technique	Huseyin Derin Adnan Menderes University, Turkey

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15:00 – 15:30 PM	B21:Growth of Mn-doped ZnO films on various substrates by rf-sputter deposition	Noriaki Matsunami Meijo University, Japan
15:30 – 16:00 PM	SESSION BREAK	
Tuesday June 11	Room B: Session 8 (General)	Chair: Noriaki Matsunami
16:00 – 16:30 PM	B22:Formation of Polycrystalline Silicon Films with Various Microstructures by Flash Lamp Annealing of Micrometer-Order-Thick Amorphous Silicon Films	Keisuke Ohdaira Japan Advanced Institute of Science and Technology, Japan
16:30 – 17:00 PM	B23:Group III-Nitride Light Emitting Semiconductor Nanostructures	Yong-Hoon Cho Korea Advanced Institute of Science and Technology (KAIST), Korea
17:00 – 17:30 PM	B24:Hierarchical ZnO/TiO ₂ Nanostructures via Novel Solution Routes and Their Applications in Dye-Sensitized Solar Cells	Xiang-Dong Gao Shanghai Institute of Ceramics, CAS, China
17:30 – 18:00 PM	B25:Growth of Cu: SnO ₂ Films via Spray Pyrolysis and their Study towards LPG and H ₂ S sensor	Kishor M. Sonawane Fergusson College, India
3CG 2013 Meeting June 12		
7:30 – 8:30	Breakfast and Poster	
Wednesday June 12	Room B: Session 9 (General)	Chair: Duk Young Jeon
8:30 – 9:00 AM	B26: Sublimation growth of the 3C-SiC on hexagonal SiC substrates	Alexander Lebedev Ioffe Institute of Russian Academy of Sciences, Russia
9:00 – 9:30 AM	B27: Laser processed substrate for stress reduction in hetero-epitaxy	Hideo Aida President of R&D at Namiki Precision Jewel Co. LTD, Japan
9:30 – 10:00 AM	B28: Orientation and property control of Tb-Fe and Tb-Dy-Fe materials during solidification in high magnetic fields	Tie Liu Northeastern University, China
10:00 – 10:30 AM	SESSION BREAK	

Conference Program Schedule Room B – 3CG 2013 Meeting

Wednesday June 12	Room B: Session 10 (Photovoltaic)	Chair: Alexander Lebedev
10:30 – 11:00 AM	B29: Crystal growth and Surface engineering of CuInS ₂ /ZnS core/shell structure quantum-dot and their application to LED	Duk Young Jeon Korea Advanced Institute of Science and Technology, Korea
11:00 – 11:30 AM	B30: Attempt to manufacture a solar cell by using a simple method of n-type doping of monocrystalline silicon	Diouma Kobor University of Ziguinchor, Senegal
11:30 – 14:00 PM	LUNCH BREAK	
Wednesday June 12	Room B: Session 11 (Energy)	Chair: Noon-Mong Hwang
14:00 – 14:30 PM	B31: Mesoscopic materials grown by MOCVD for thermoelectric power generation: Semiconductor nanowire networks and semi-metallic/semiconductor thin films	Nobuhiko P. Kobayashi University of California, USA
14:30 – 15:00 PM	B32: Growth Methodologies for Overcoming the Challenges of Phase Separation and p-type Doping in InGaN	William Alan Doolittle Georgia Institute of Technology, USA
15:00 – 15:30 PM	B33: Designing nanocomposite anodes for Li-ion batteries	Alexey Glushenkov Deakin University, Australia
15:30 – 16:00 PM	SESSION BREAK	
Wednesday June 12	Room B: Session 12 (Semiconductor)	Chair: Alexey Glushenkov
16:00 – 16:30 PM	B34: Charge-enhanced diffusion: insight from the deposition behavior of charged nanoparticles during chemical vapor deposition	Noon-Moon Hwang Seoul National University, Korea
16:30 – 17:00 PM	B35: Epitaxial growth of vertical III-V semiconductor nanowires on Si and graphene	Helge Weman Norwegian University of Science and Technology, Norway
17:00 – 17:30 PM	B36: Corrosion Resistance of Dendritic and Eutectic Al-Cu Alloys as a Function of Microstructure	Alicia Esther Ares National University of Misiones, Argentina

Conference Program Schedule Room B – 3CG 2013 Meeting

Thursday June 13	Social Network Events
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<p>3CG 2013 MEETING</p> <p>June 10-13, 2013</p> <p>The Westin Resort & Spa, Cancun, Mexico</p> <p>Room C</p>		
<p>Conference Onsite Registration</p> <p>The Westin Resort & Spa</p> <p>14:00 - 18:00 PM</p> <p>June 9</p>		
<p>3CG 2013 Meeting June 10</p>		
7:20 – 8:20	Breakfast	
Monday June 10 8:20 - 8:30 AM	Opening	
Monday June 10	Room C: Session 1 (General)	Chair: Hiroshi Fujioka
8:30 – 9:00 AM	C1: Semi-polar growth of InN on GaAs (11n) substrate by MOVPE	Hisashi Murakami Tokyo University of Agriculture and Technology, Japan
9:00 – 9:30 AM	C2: Structure and dynamics of multifunctional materials with neutron scatterings	Dehong Yu Australian Nuclear Science and Technology Organisation, Australia
9:30 – 10:00 AM	C3: Crystal growth for super high-efficiency multi-junction Solar cells	Yoshio Ohshita Toyota Technological Institute, Japan
10:00 – 10:30 AM	SESSION BREAK	

Conference Program Schedule Room C – 3CG 2013 Meeting

Monday June 10	Room C: Session 2 (Semiconductor)	Chair: Hisashi Murakami
10:30 – 11:00 AM	C4: Epitaxial Growth of High Quality Nitride Films by Pulsed	Hiroshi Fujioka The University of Tokyo, Japan
11:00 – 11:30 AM	C5: High performance nitride-based HFET photosensors	Motoaki Iwaya Meijo University, Japan
11:30 – 12:00 AM	C6: Precise control of strain by interface formation in type-II InAs/GaSb superlattice	Janusz Kaniewski Institute of Electron Technology, Poland
12:00 - 14:00 PM	LUNCH BREAK	
Monday June 10	Room C: Session 3 (Semiconductor)	Chair: Fabio A. Ferri
14:00 – 14:30 PM	C7: Various efforts for DUV and VUV lasers	Nobuhiko Sarukura Osaka University, Japan
14:30 – 15:00 PM	C8: Fast SiC growth rate epitaxy by chloride precursors	Francesco La Via CNR-IMM sezione di Catania, Italy
15:00 – 15:30 PM	C9: P reparation of free-standing GaN substrates from thick GaN layers crystallized by Hydride Vapor Phase Epitaxy on ammonothermally grown GaN seeds	Michal Bockowski Institute of High Pressure Physics PAS , TopGaN Ltd, Poland
15:30 – 16:00 PM	SESSION BREAK	
Monday June 10	Room C: Session 4 (General)	Chair: Michal Bockowski
16:00 – 16:30 PM	C10: Magnetic impurities in group-IV and group-III-V semiconductors	Fabio A. Ferri University of Arkansas, USA
16:30 – 17:00 PM	C11: Growth controlled of monocrystalline V ₂ O ₅ nanowires by solvothermal reduction	Patricia Joshi Santiago Universidad Nacional Autónoma de México, Mexico

Conference Program Schedule Room C – 3CG 2013 Meeting

17:00 – 17:30 PM	C12: On the road towards GaAs nanowire integration: Au-free growth and crystal phase purity	Stefano Filo Ambrosini Università di Trieste, Italia
17:30 – 18:00 PM	C13: Quantum size stabilization during initial growth of metal films	Bene Poelsema University of Twente, Netherlands
3CG 2013 Meeting June 11		
7:30 – 8:30	Breakfast and Poster	
Tuesday June 11	Room C: Session 5 (Single Crystal)	Chair: Seungho Park
8:30 – 9:00 AM	C14: Influence of silver deficiency and excess on quality, dielectric properties and phase transitions of AgNbO ₃	Antoni Kania Zakład Fizyki Ferroelektryków Uniwersytecka, Katowice
9:00 – 9:30 AM	C15: Growth of High-Purity CaWO ₄ Single Crystals for the Low-Temperature Dark Matter Research Experiments CRESST and EURECA	Andreas Erb Technische Universität München, Germany
9:30 – 10:00 AM	C16: Colloidal Heterostructured Nanocrystals: Synthesis, Properties and Applications	P. Davide COZZOLI Università del Salento, Italy
10:00 – 10:30 AM	SESSION BREAK	
Tuesday June 11	Room C: Session 6 (Single Crystals)	Chair: Raoul van Gastel
10:30 – 11:00 AM	C17: Direct visualization of subcritical nuclei in molecular film growth	Raoul van Gastel University of Twente, Netherlands
11:00 – 11:30 AM	C18: Current Stage on Flash Lamp Crystallization for LTPS on Large-Scale Glass Backplanes up to 8th Gen	Seungho Park Hongik University, Korea
11:30 – 12:00 AM	C19: Direct Growth of porous hollow palladium nanoparticles on ITO substrate using LPD process	Aamna Balouch University Kebangsaan Malaysia, Malaysia
12:00 – 14:00 PM	LUNCH BREAK	

Conference Program Schedule Room C – 3CG 2013 Meeting

Tuesday June 11	Room C: Session 7 (Single Crystals)	Chair: Yuji Ohashi
14:00 – 14:30 PM	C20:Single-Crystal Structure and Polymorphism Screening of Racemate Menthol and its Levorotatory Optical Isomer	Yohann Corvis Paris Descartes University, France
14:30 – 15:00 PM	C21:The Ultra-high electrical conductivity in metal single crystals and mixed crystals	Se-Young Jeong Pusan National University, Korea
15:00 – 15:30 PM	C22:Optimization of growth of relaxor-based single crystals used for ultrasonic transducer application	Haosu Luo Shanghai Institute of Ceramics, CAS, China
15:30-16:00 PM	SESSION BREAK	
Tuesday June 11	Room C: Session 8 (Single Crystals)	Chair: Haosu Luo
16:00 – 16:30 PM	C23:Single Crystal Growth of 1D and 2D Pnictide and Chalcogenide Superconductors	Bing Lv University of Houston, USA
16:30 – 17:00 PM	C24:Analyzing Crystals by Ultrasonic Microspectroscopy	Yuji Ohashi Tohoku University, Japan
17:00 – 17:30 PM	C25:Dynamics of polar nanoregions in lead free relaxor ferroelectric single crystals	Chandra Shekhar Pandey Ruhr University Bochum, Germany
17:30 – 18:00 PM	C26: The diffraction geometry and measurement of intensities in the Rotation Electron Diffraction Technique	Mika Buxhuku University of Stavanger, Norway
3CG 2013 Meeting June 12		
7:30 – 8:30	Breakfast and Poster	
Wednesday June 12	Room C: Session 9 (Crystals)	Chair: Mika Buxhuku
8:30 – 9:00 AM	C27: Ammonothermal Growth of Bulk GaN Crystals	Tadao Hashimoto SixPoint Materials, Inc., USA

Conference Program Schedule Room C – 3CG 2013 Meeting

9:00 – 9:30 AM	C28:Traveling Solvent Floating Zone (TSFZ) Growth of Various Superconducting Single Crystals	Chengtian Lin Max-Planck-Institute for Solid State Physics, Germany
9:30 – 10:00 AM	C29:Electron localization in anatase and rutile TiO ₂	Cesare Franchini University of Vienna, Austria
10:00 – 10:30 AM	SESSION BREAK	
Wednesday June 12	Room C: Session 10 (General)	Chair: Tadao Hashimoto
10:30 – 11:00 AM	C30:Dynamic CN-bridged coordination networks	Beata Nowicka Jagiellonian University, Poland
11:00 – 11:30 AM	C31:Electrical properties of fullerene doped GaAs pin diodes grown by MBE	Jiro Nishinaga Waseda University, Japan
11:30 – 12:00 AM	C32:Growth, physical and photo-electrical properties of solid solutions CuInS ₂ -ZnIn ₂ S ₄	Vaidotas KAŽUKAUSKAS Vilnius University, Lithuania
12:00 – 14:00 PM	LUNCH BREAK	
Wednesday June 12	Room C: Session 11 (Single Crystal)	Chair: Peter Schall
14:00 – 14:30 PM	C33:Single crystal growth and characterization of superconducting LiFeAs and its substitution variants	Sabine Wurmehl Leibniz Institute for Solid State and Materials Research Dresden, Germany
14:30 – 15:00 PM	C34:Effects of impurities on the properties of sapphire	Radion Mogilevsky Emerging Material Technologies, Inc USA
15:00 – 15:30 PM	C35:Development of functional single crystals by micro-pulling-down method	Yuui Yokota Tohoku University, Japan
15:30 – 16:00 PM	SESSION BREAK	

Conference Program Schedule Room C – 3CG 2013 Meeting

Wednesday June 12	Room C: Session 12 (Single Crystal)	Chair: Sabine Wurmehl
16:00 – 16:30 PM	C36:Single Crystal Growth of Organic Semiconductors	Shu Hotta Kyoto Institute of Technology, Japan
16:30 – 17:00 PM	C37:Direct "atomic-scale" observation of crystallization in colloidal systems	Peter Schall University of Amsterdam, Netherlands
17:00 – 17:30 PM	C38:Pure and doped aromatic derivatives crystals growth and characterization	Anca Stanculescu National Institute of Materials Physics, Romania
17:30 – 18:00 PM	C39:High-pressure crystal growth and electromagnetic properties of perovskite oxides and related compounds	Kazunari Yamaura Hokkaido University, Japan
Thursday June 13	Social Network Events	

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<p>Posters</p>		
P1	Carbon Nanotubes Noncovalently Functionalized with Human Serum Albumin as Supports for Silver Nanoparticles	A. Rodríguez-Galván Universidad Nacional Autónoma de México, Mexico
P2	C60 Fullerene Covalently Functionalized with Aromatic Amine Molecules in the Gas Phase	V. Meza-Laguna Universidad Nacional Autónoma de México, Mexico
P3	Covalent Functionalization of Carbon Nanomaterials with Crown Ethers	L. V. Henao-Holguín Universidad Nacional Autónoma de México, Mexico
P4	Interaction of Silver Nanoparticles with Short Peptides: A DFT Study	F. F. Contreras-Torres Universidad Nacional Autónoma de México, Mexico
P5	Functionalization of Multi-Walled Carbon Nanotubes and Buckypaper with Aromatic Amines	I. J. Ramírez-Calera Universidad Nacional Autónoma de México, Mexico
P6	Noncovalent Functionalization of Carbon Nanotubes with a Ni(II) Tetraaza[14] annulene Complex	V. Henao-Holguín Universidad Nacional Autónoma de México,

Conference Program Schedule Poster – 3CG 2013 Meeting

		Mexico
P7	Noncovalent Nanohybrid of Graphene with a Ni(II) Tetraaza[14]annulene Complex	M. Martínez-Herrera Universidad Nacional Autónoma de México, Mexico
P8	Macrostructure and magnetic properties of Mn-Sb alloys prepared by directional solidification with a varying growth velocity	Pengfei Gao Northeastern University China
P9	Specific Surface Free Energy and Morphology of Barium Chlorapatite Single Crystals	Mika Yoshida Shinshu University, Japan
P10	The Specific Surface Free Energy of Synthesized Quartz	Keiko Takahashi Shinshu University Japan
P11	Cadmium telluride nanostructures by Electrochemical Synthesis	Ramesh S. Kapadnis University of Pune, India
P12	Optical transmission of Er ³⁺ ions excited by white light via square nanohole arrays	V.A.G. Rivera Universidade de São Paulo Brazil